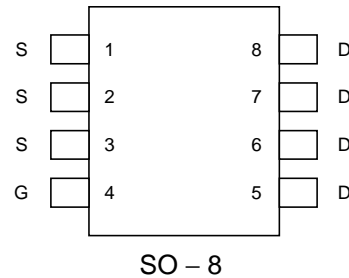


N-Channel Enhancement Mode MOSFET

Features

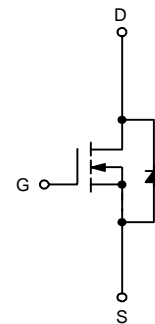
- 25V/16A , $R_{DS(ON)} = 7m\Omega(\text{typ.}) @ V_{GS} = 4.5V$
- Super High Dense Advanced Cell Design for Extremely Low $R_{DS(ON)}$
- Reliable and Rugged
- SOP-8 Package

Pin Description



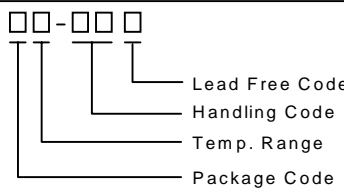
Applications

- Power Management in Desktop Computer or DC/DC Converters.



N-Channel MOSFET

Ordering and Marking Information

APM4230		Package Code K : SO - 8 Operating Junction Temp. Range C : -55 to 150 °C Handling Code TU : Tube TR : Tape & Reel Lead Free Code L : Lead Free Device Blank : Original Device
APM4230K :	<div style="border: 1px solid black; padding: 2px; display: inline-block;"> APM4230 XXXXX </div>	XXXXX - Date Code

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Rating	Unit
V_{DSS}	Drain-Source Voltage	25	V
V_{GSS}	Gate-Source Voltage	± 20	
I_D^*	Maximum Drain Current – Continuous	16	A
I_{DM}	Maximum Drain Current – Pulsed	60	

* Surface Mounted on FR4 Board, $t \leq 10$ sec.

ANPEC reserves the right to make changes to improve reliability or manufacturability without notice, and advise customers to obtain the latest version of relevant information to verify before placing orders.

Absolute Maximum Ratings (Cont.) ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Rating	Unit
P_D	Maximum Power Dissipation	$T_A=25^\circ\text{C}$	2.5
		$T_A=100^\circ\text{C}$	1.0
T_J	Maximum Junction Temperature	150	$^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
$R_{\theta JA}^*$	Thermal Resistance – Junction to Ambient	50	$^\circ\text{C/W}$

Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Condition	APM4230			Unit
			Min.	Typ.	Max.	
Static						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_{DS}=250\mu\text{A}$	25			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=20V, V_{GS}=0V$			1	μA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_{DS}=250\mu\text{A}$	1	1.5	2	V
I_{GSS}	Gate Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$			± 100	nA
$R_{DS(ON)}^a$	Drain-Source On-state Resistance	$V_{GS}=4.5V, I_{DS}=16A$		7	8	m Ω
		$V_{GS}=4.5V, I_{DS}=16A$ $T_J=125^\circ\text{C}$		10.5	12	
V_{SD}^a	Diode Forward Voltage	$I_S=16A, V_{GS}=0V$		0.7	1.2	V
Dynamic^b						
Q_g	Total Gate Charge	$V_{DS}=15V, I_{DS}=16A$ $V_{GS}=4.5V,$		30	40	nC
Q_{gs}	Gate-Source Charge			13		
Q_{gd}	Gate-Drain Charge			10		
$t_{d(ON)}$	Turn-on Delay Time	$V_{DD}=15V, I_{DS}=1A,$ $V_{GEN}=10V, R_G=6\Omega$		13	20	ns
T_r	Turn-on Rise Time			9	15	
$t_{d(OFF)}$	Turn-off Delay Time			43	66	
T_f	Turn-off Fall Time			14	28	
C_{iss}	Input Capacitance	$V_{GS}=0V$		3000		pF
C_{oss}	Output Capacitance	$V_{DS}=15V$		660		
C_{rss}	Reverse Transfer Capacitance	Frequency=1.0MHz		330		

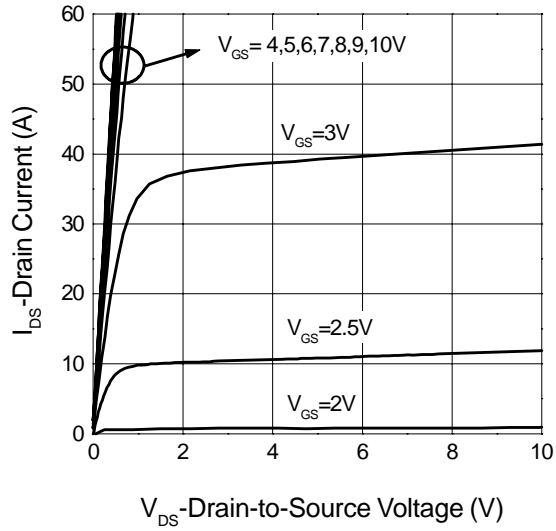
Notes

^a : Pulse test ; pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$

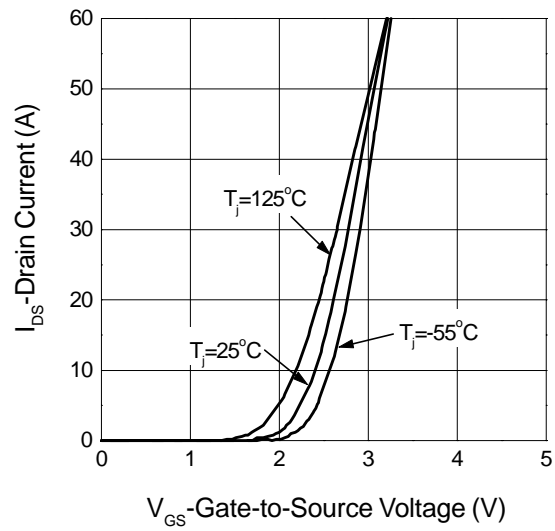
^b : Guaranteed by design, not subject to production testing

Typical Characteristics

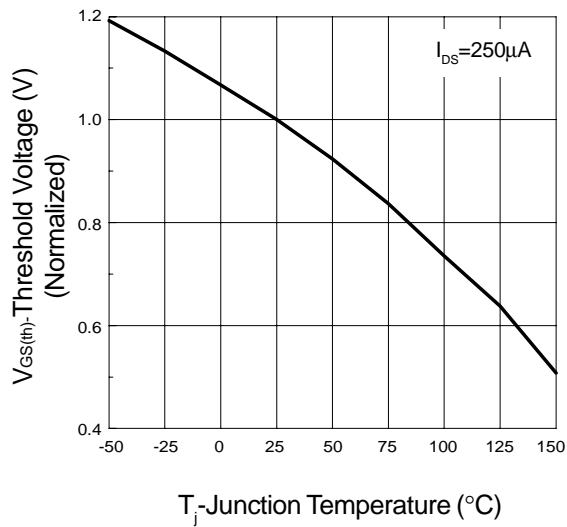
Output Characteristics



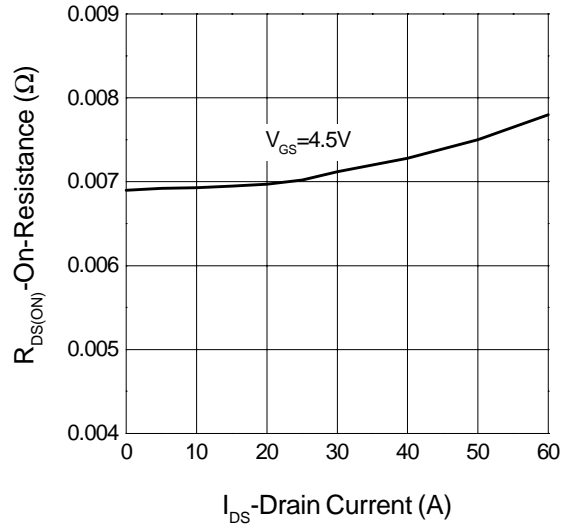
Transfer Characteristics



Threshold Voltage vs. Junction Temperature

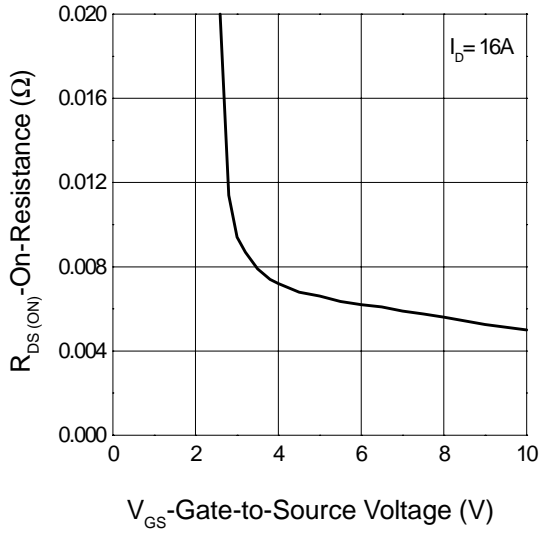


On-Resistance vs. Drain Current

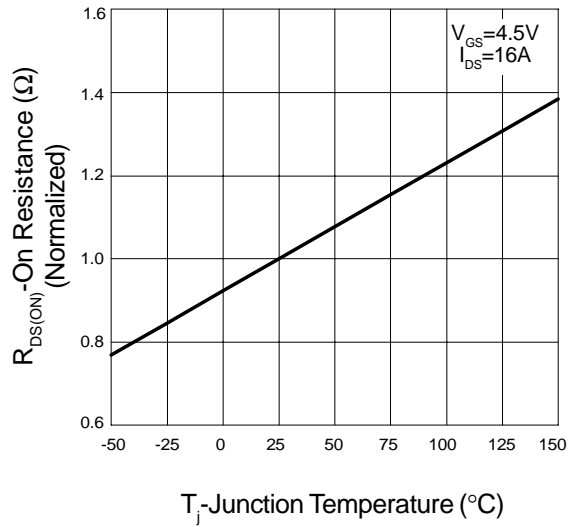


Typical Characteristics (Cont.)

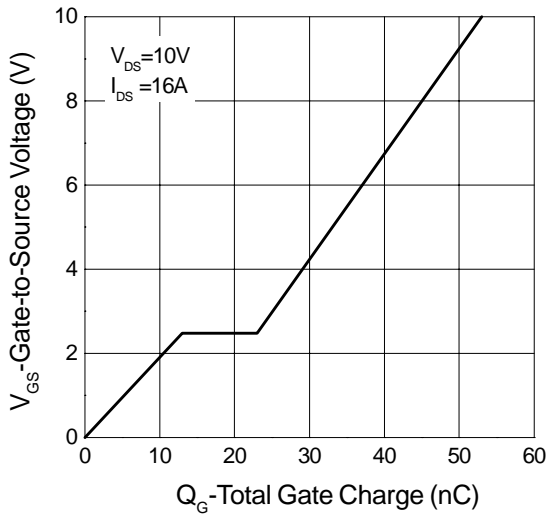
On-Resistance vs. Gate-to-Source Voltage



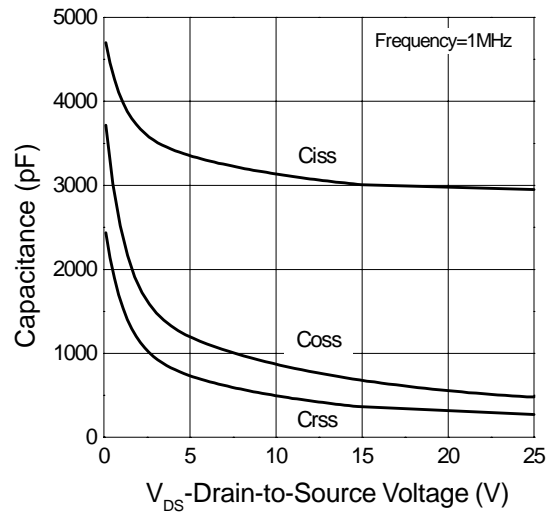
On-Resistance vs. Junction Temperature



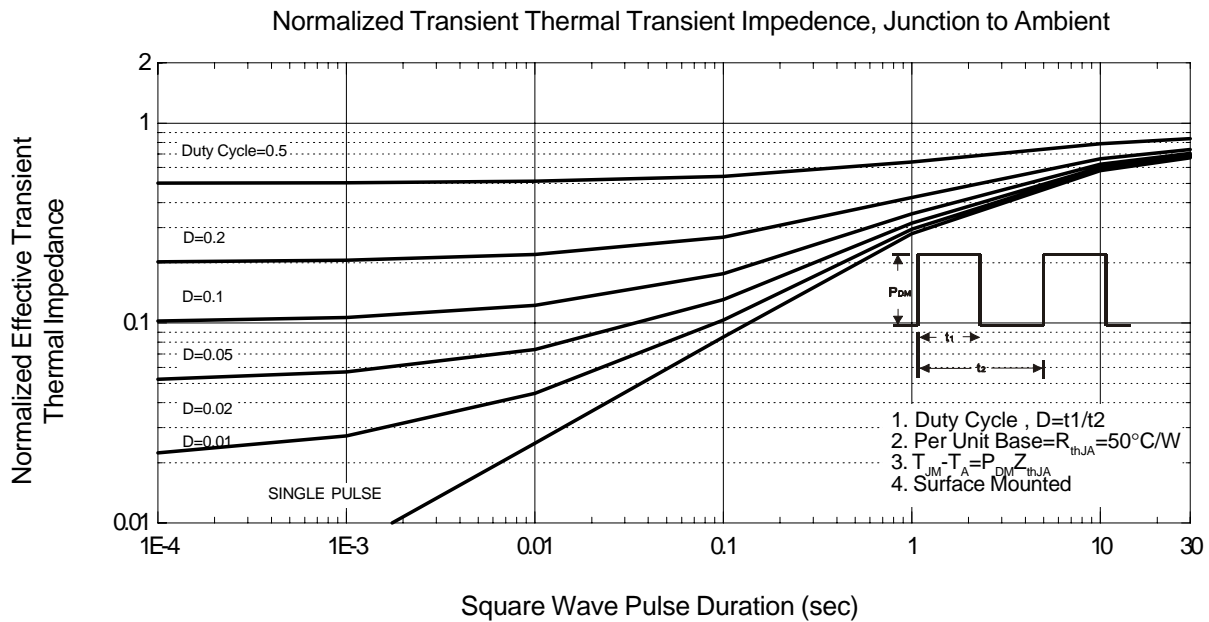
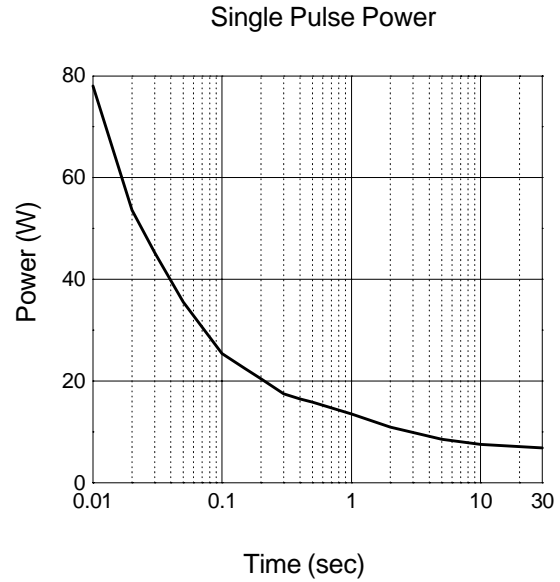
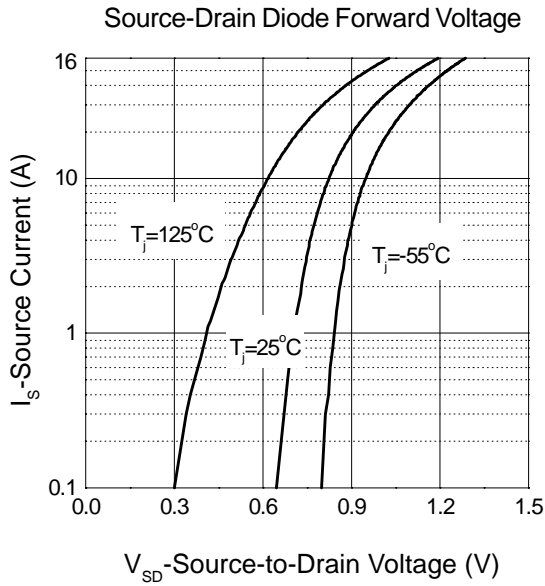
Gate Charge



Capacitance

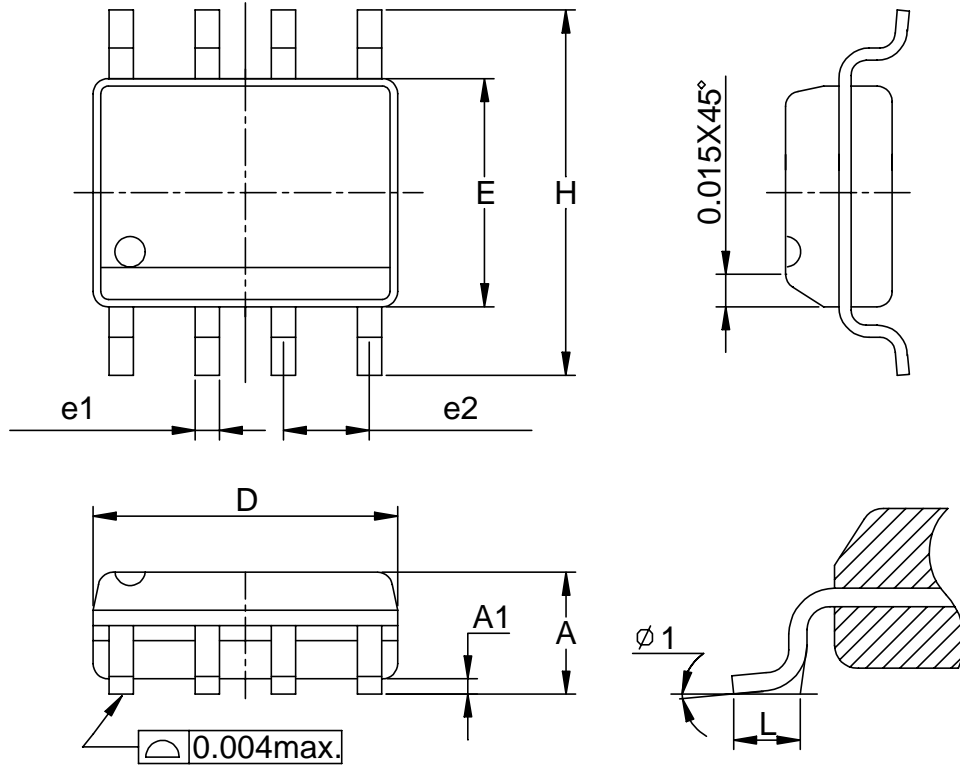


Typical Characteristics (Cont.)



Package Informaion

SOP-8 pin (Reference JEDEC Registration MS-012)



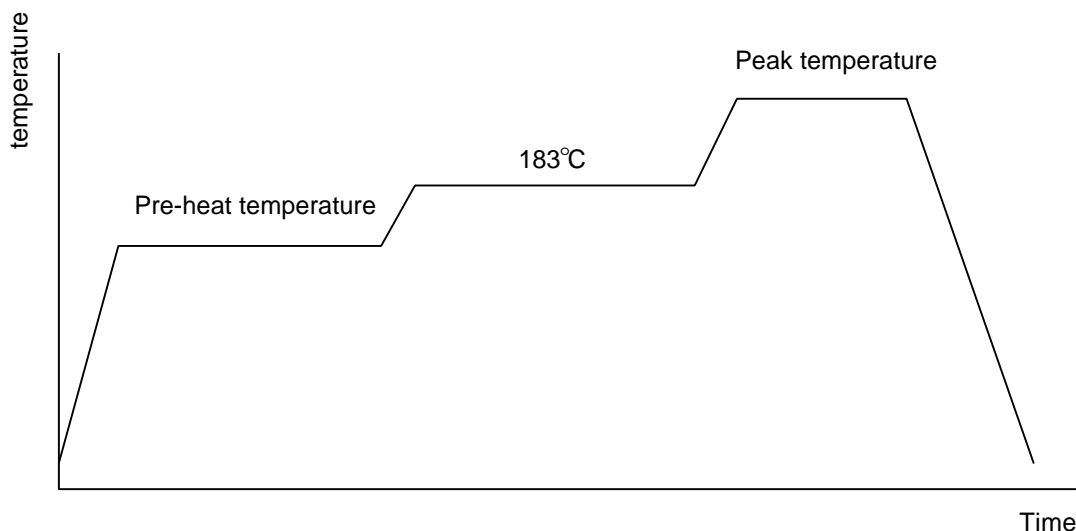
Dim	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	1.35	1.75	0.053	0.069
A1	0.10	0.25	0.004	0.010
D	4.80	5.00	0.189	0.197
E	3.80	4.00	0.150	0.157
H	5.80	6.20	0.228	0.244
L	0.40	1.27	0.016	0.050
e1	0.33	0.51	0.013	0.020
e2	1.27BSC		0.50BSC	
φ 1	8°		8°	

Physical Specifications

Terminal Material	Solder-Plated Copper (Solder Material : 90/10 or 63/37 SnPb)
Lead Solderability	Meets EIA Specification RSI86-91, ANSI/J-STD-002 Category 3.

Reflow Condition (IR/Convection or VPR Reflow)

Reference JEDEC Standard J-STD-020A APRIL 1999



Classification Reflow Profiles

	Convection or IR/ Convection	VPR
Average ramp-up rate(183 °C to Peak)	3 °C/second max.	10 °C /second max.
Preheat temperature 125 ± 25 °C)	120 seconds max.	
Temperature maintained above 183 °C	60 ~ 150 seconds	
Time within 5 °C of actual peak temperature	10 ~ 20 seconds	60 seconds
Peak temperature range	220 +5/-0 °C or 235 +5/-0 °C	215~ 219 °C or 235 +5/-0 °C
Ramp-down rate	6 °C /second max.	10 °C /second max.
Time 25 °C to peak temperature	6 minutes max.	

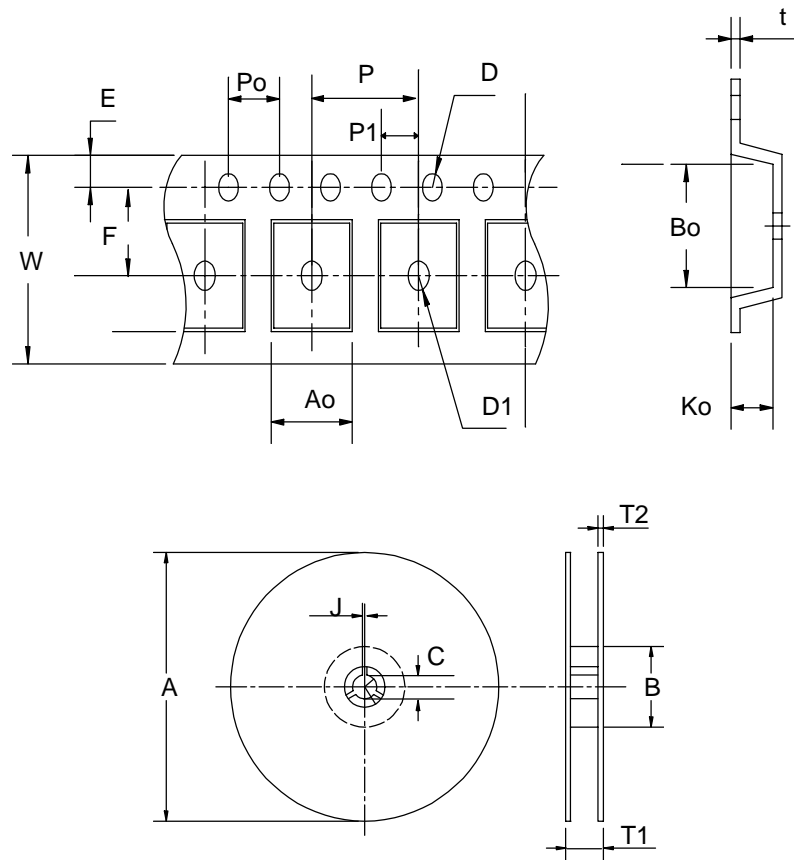
Package Reflow Conditions

pkg. thickness ≥ 2.5mm and all bags	pkg. thickness < 2.5mm and pkg. volume ≥ 350 mm	pkg. thickness < 2.5mm and pkg. volume <
Convection 220 +5/-0 °C		Convection 235 +5/-0 °C
VPR 215-219 °C		VPR 235 +5/-0 °C
IR/Convection 220 +5/-0 °C		IR/Convection 235 +5/-0 °C

Reliability test program

Test item	Method	Description
SOLDERABILITY	MIL-STD-883D-2003	245°C, 5 SEC
HOLT	MIL-STD 883D-1005.7	1000 Hrs Bias @ 125°C
PCT	JESD-22-B, A102	168 Hrs, 100% RH, 121°C
TST	MIL-STD 883D-1011.9	-65°C ~ 150°C, 200 Cycles

Carrier Tape & Reel Dimension



Application	A	B	C	J	T1	T2	W	P	E
TO-252	330±3	100 ± 2	13 ± 0.5	2 ± 0.5	16.4 +0.3 -0.2	2.5± 0.5	16 + 0.3 16 - 0.1	8 ± 0.1	1.75± 0.1
	F	D	D1	Po	P1	Ao	Bo	Ko	t
	7.5 ± 0.1	1.5± 0.1	1.5+ 0.25	4.0 ± 0.1	2.0 ± 0.1	6.8 ± 0.1	10.4± 0.1	2.5± 0.1	0.3±0.05

(mm)

Cover Tape Dimensions

Application	Carrier Width	Cover Tape Width	Devices Per Reel
TO- 252	16	13.3	2500

Customer Service

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